

FIG. 1

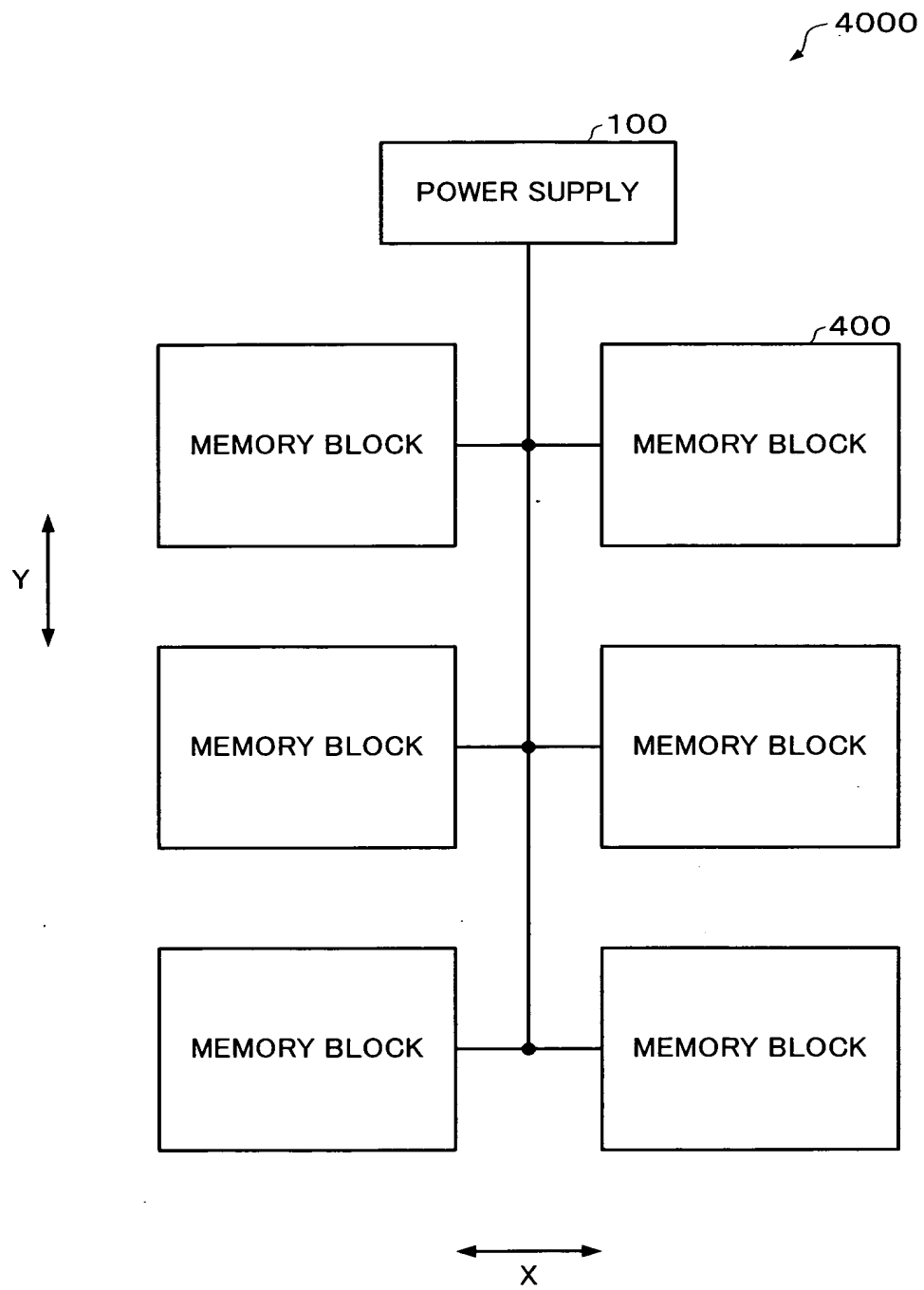


FIG. 2

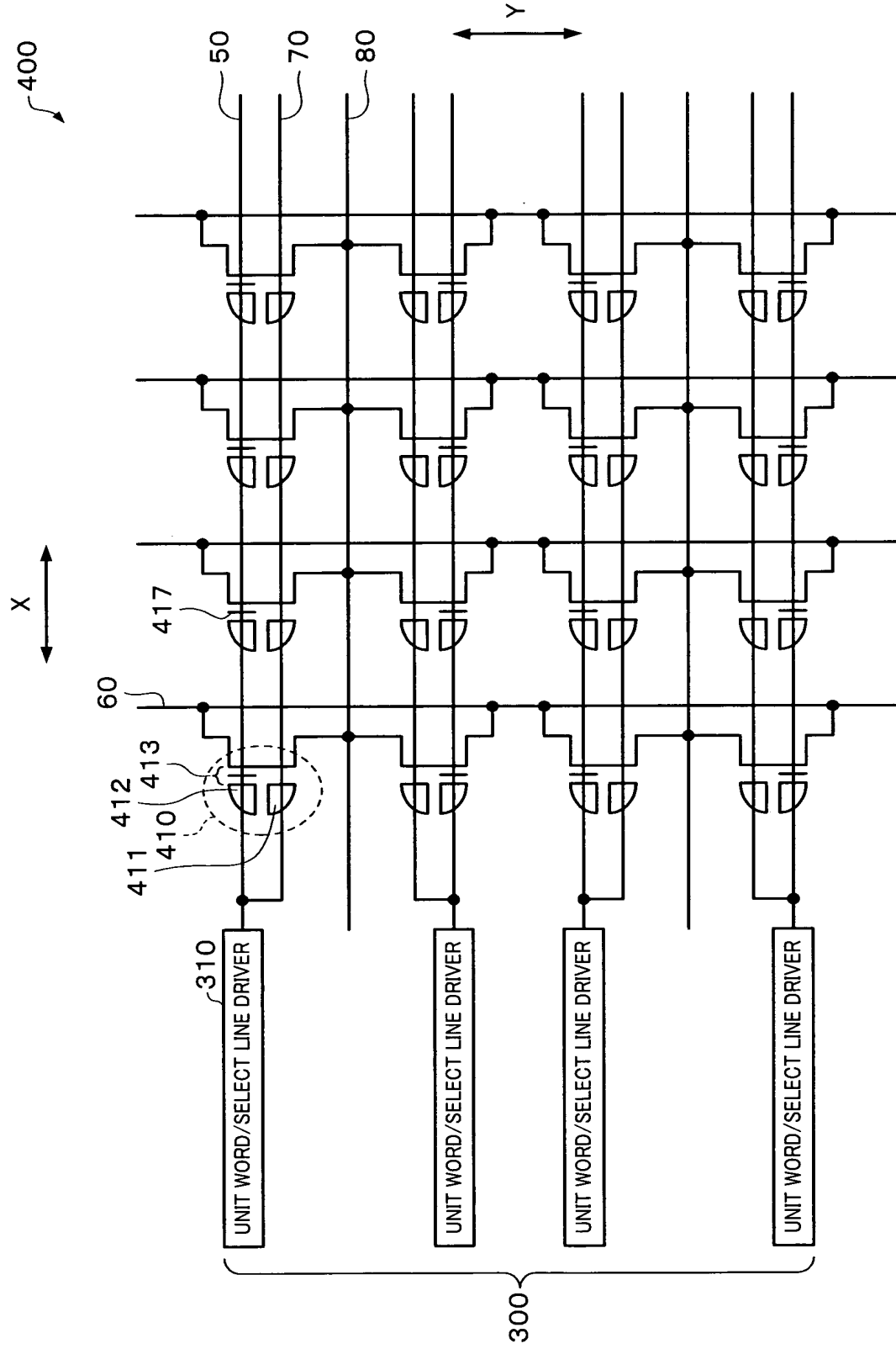


FIG. 3

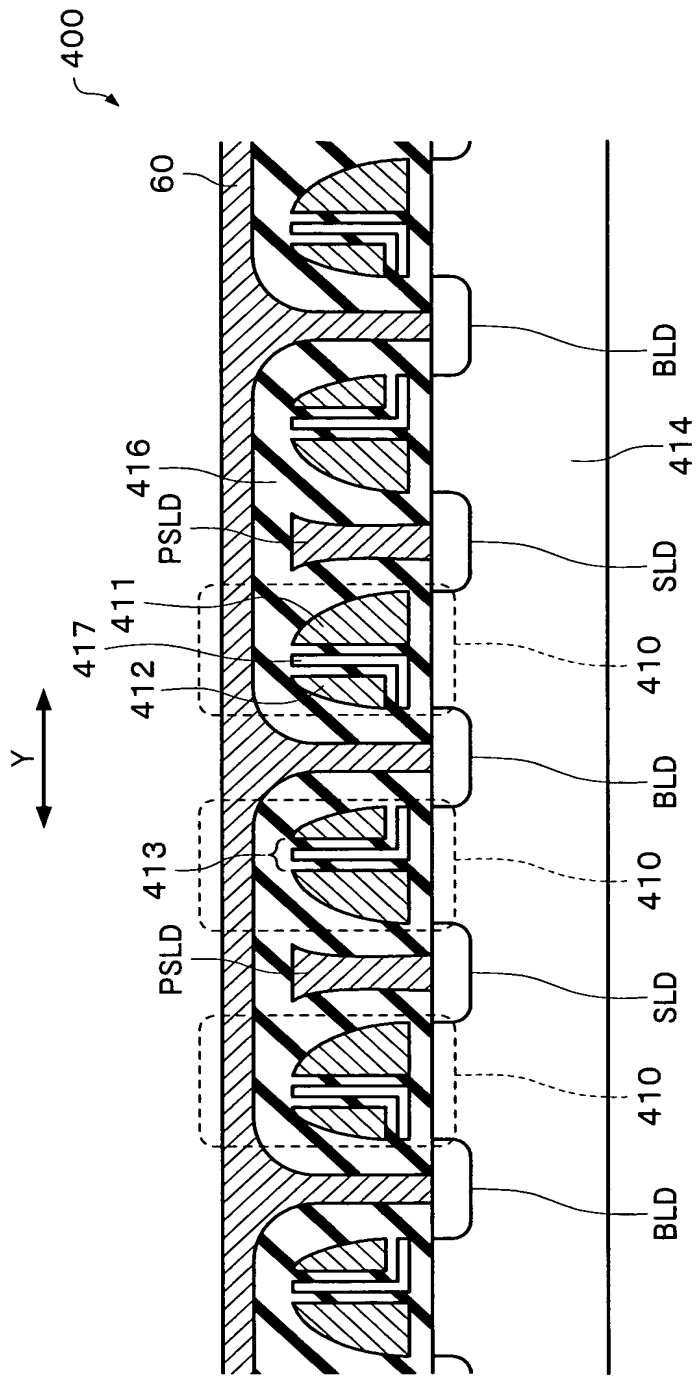
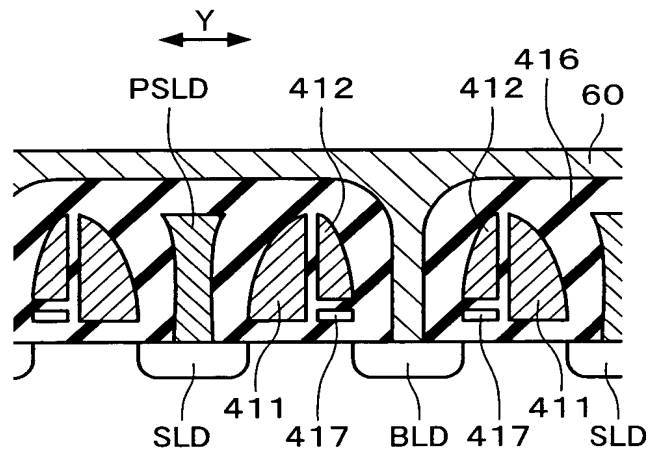


FIG. 4



A cross-sectional view of a semiconductor device. The device consists of a stack of layers. The top layer is labeled 5D. Below it is a layer 5B, which contains a central region 70. This region 70 contains WSCNT (wavy lines) and BCNT (cross-hatched areas). The layer 5B is flanked by regions 50(412) and 50(411). Below layer 5B is another layer 5C, which also contains a central region 70. The bottom layer is labeled 60. The device is labeled with dimensions 50, 60, and 70. A coordinate system X-Y is shown, with X being the vertical axis and Y being the horizontal axis. The layers are labeled 5D, 5B, and 5C. The central region is labeled 70. The regions on either side of the central region are labeled 50(412) and 50(411). The bottom layer is labeled 60. The top layer is labeled 5D. The device is labeled with dimensions 50, 60, and 70. A coordinate system X-Y is shown, with X being the vertical axis and Y being the horizontal axis.

411 412 411 416 PSLD SLD 419

FIG. 6

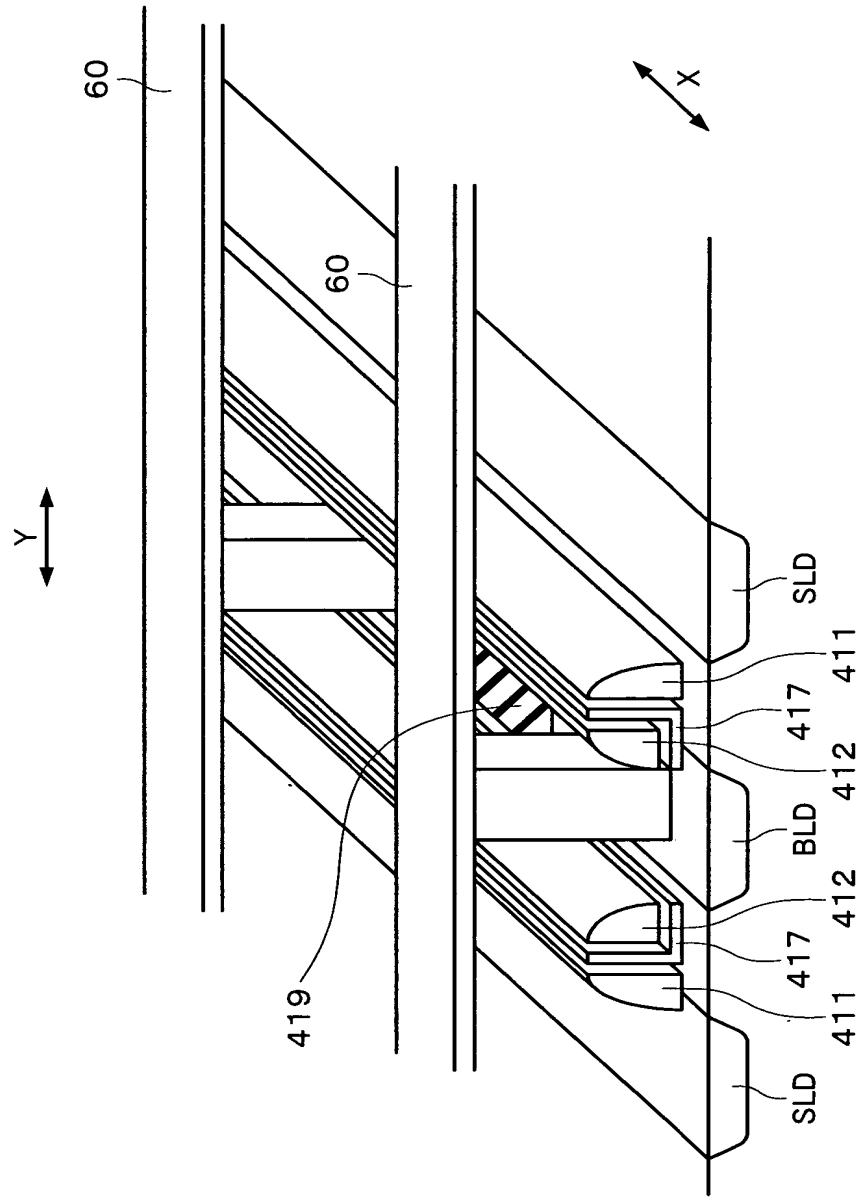


FIG. 7

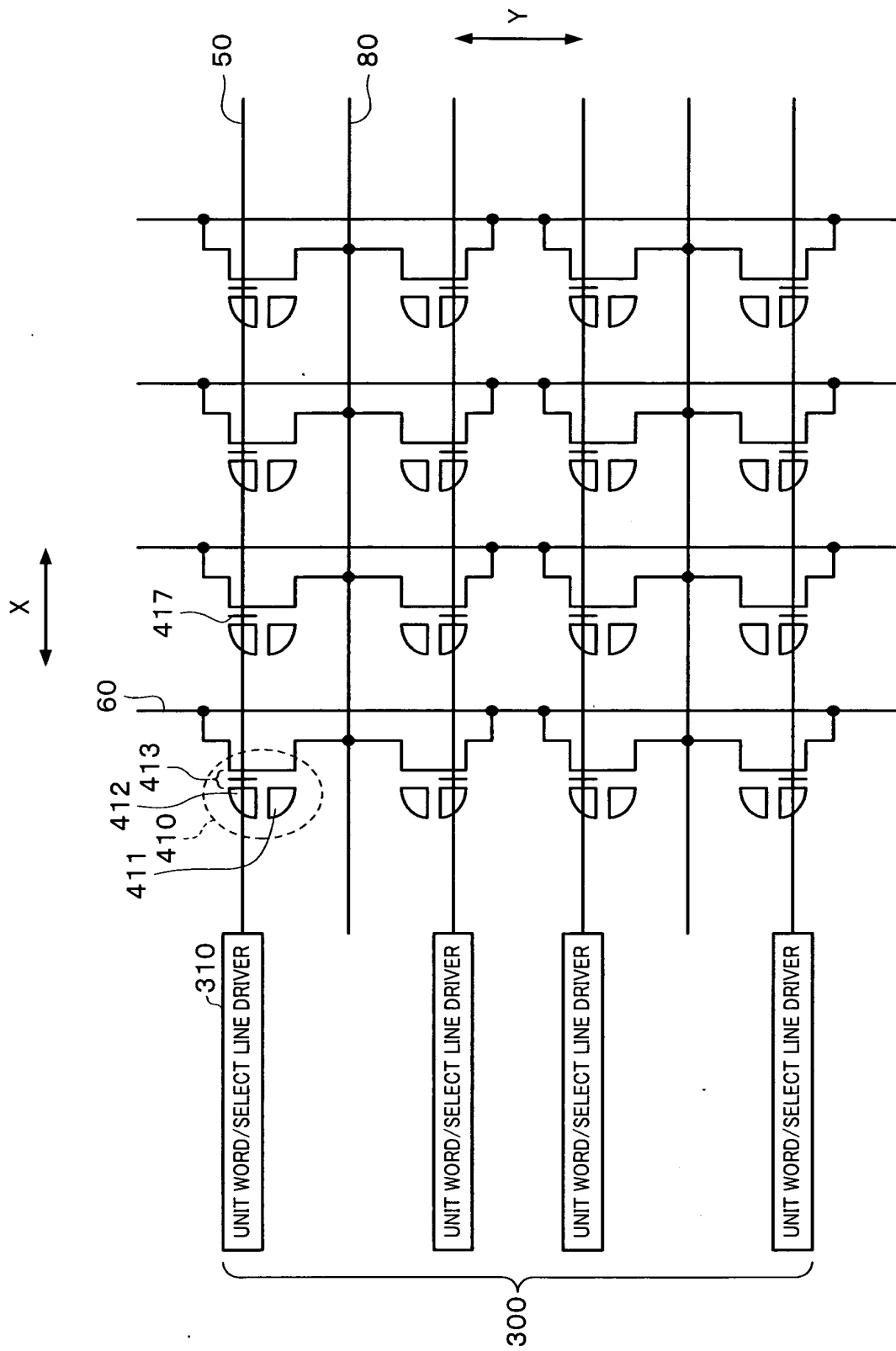


FIG. 8

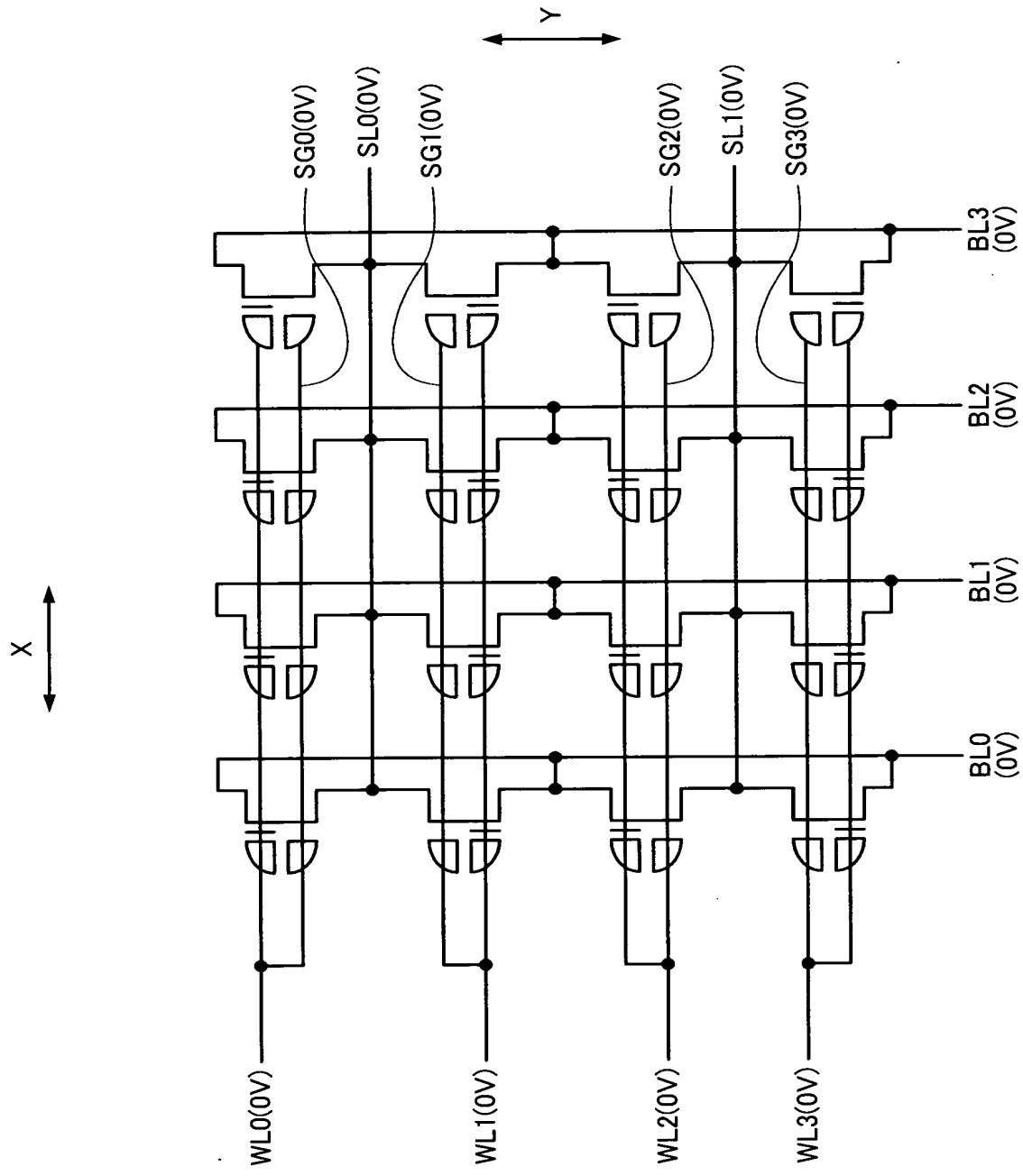




FIG. 9

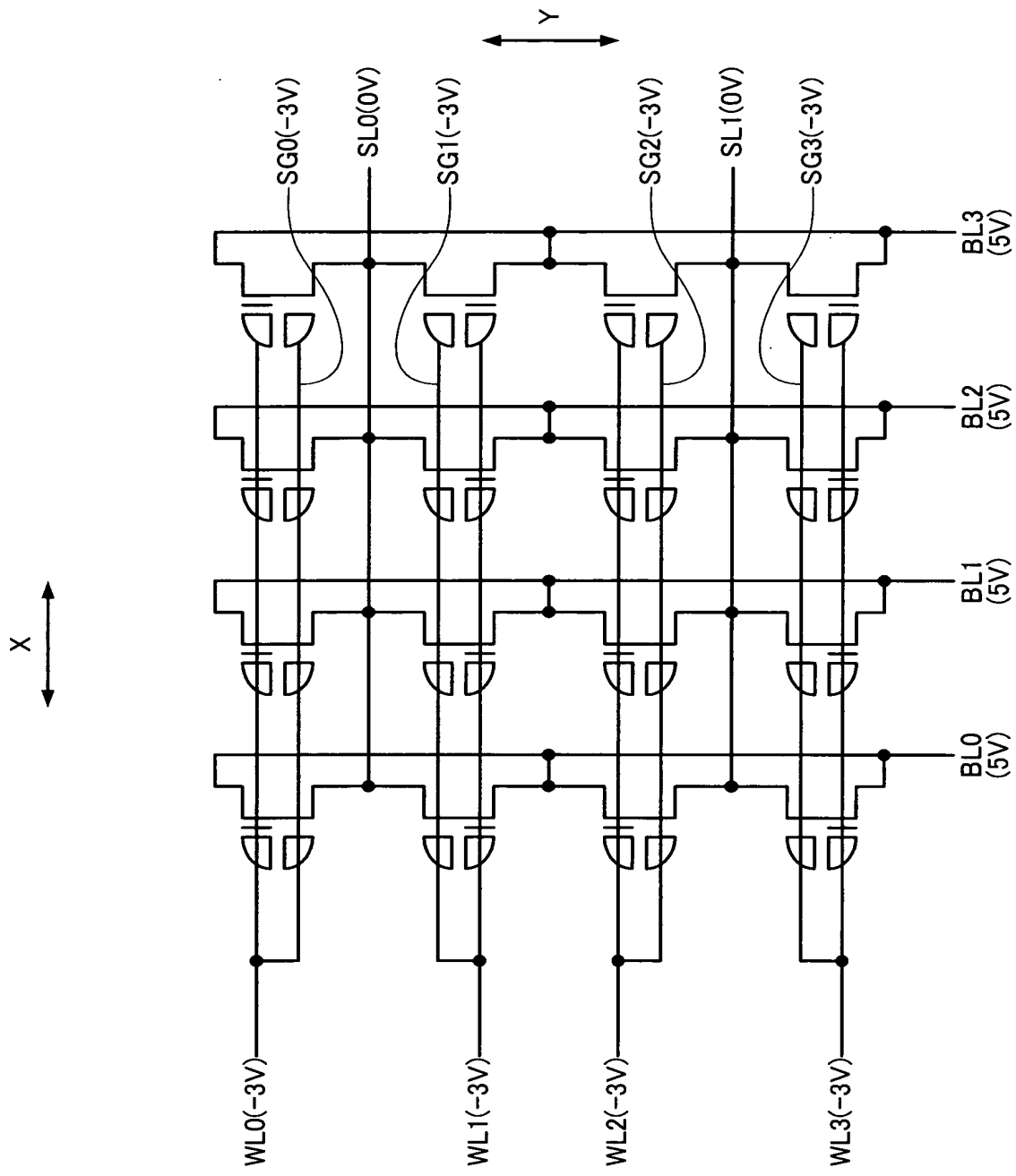


FIG. 10

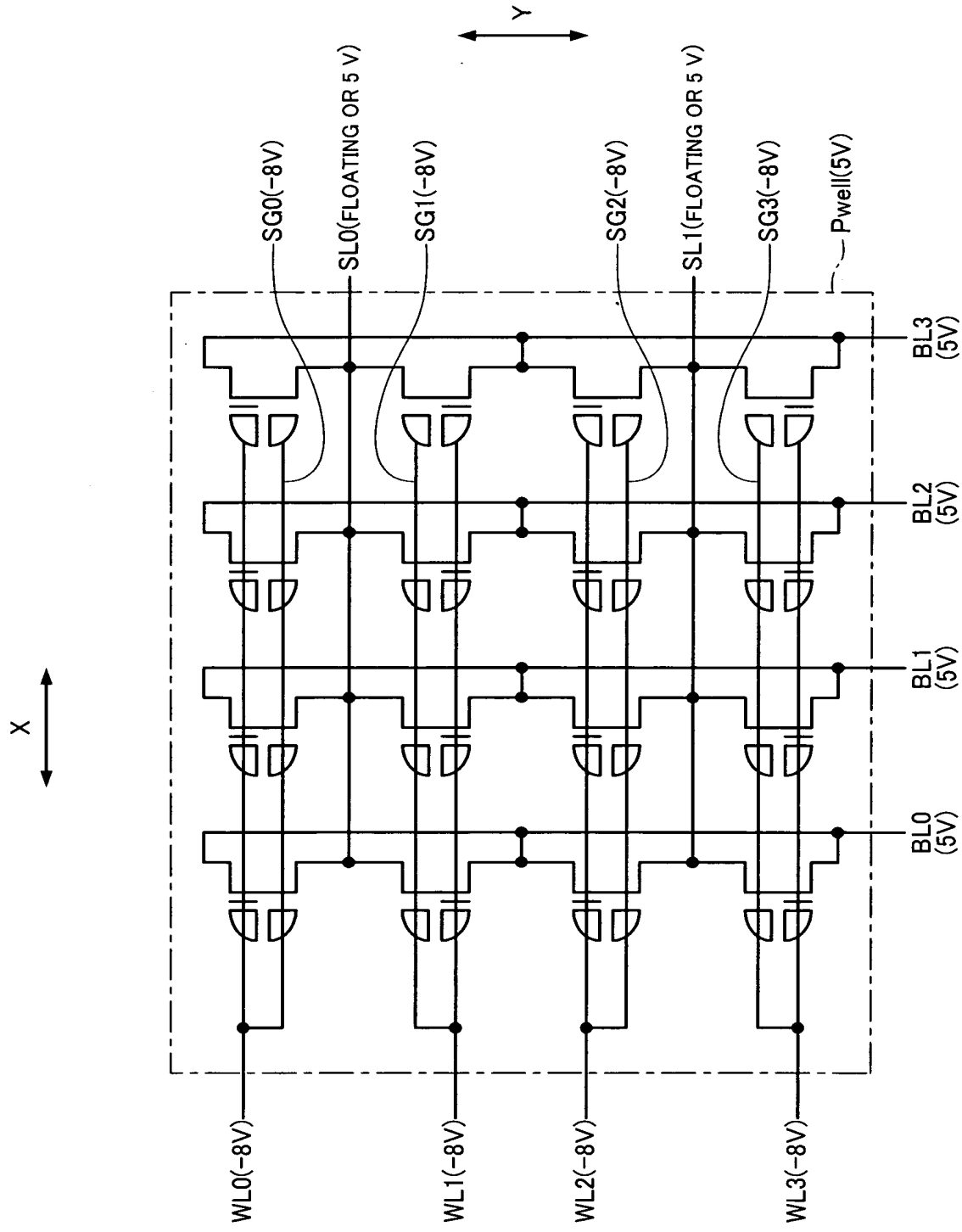


FIG. 11

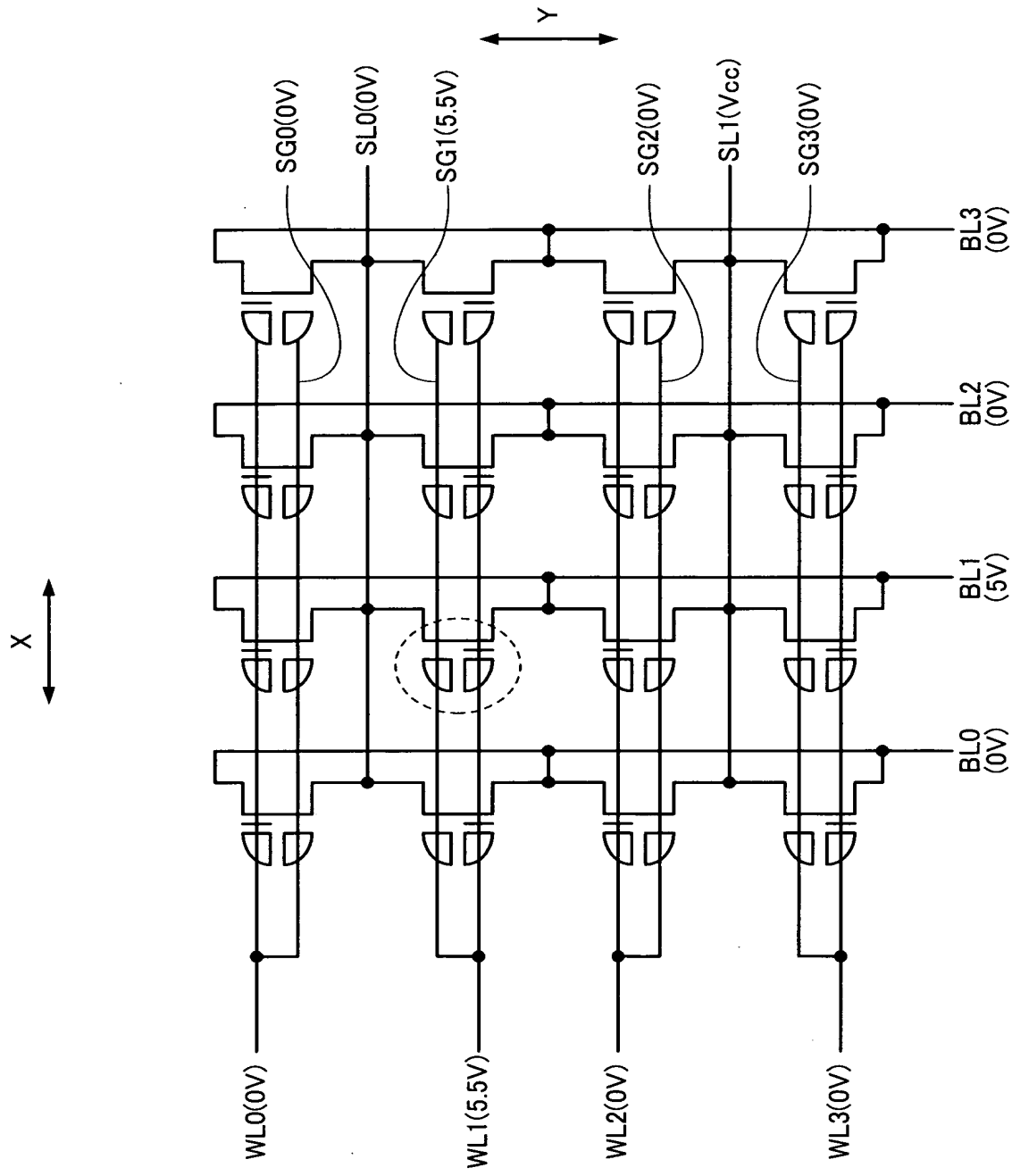


FIG. 12

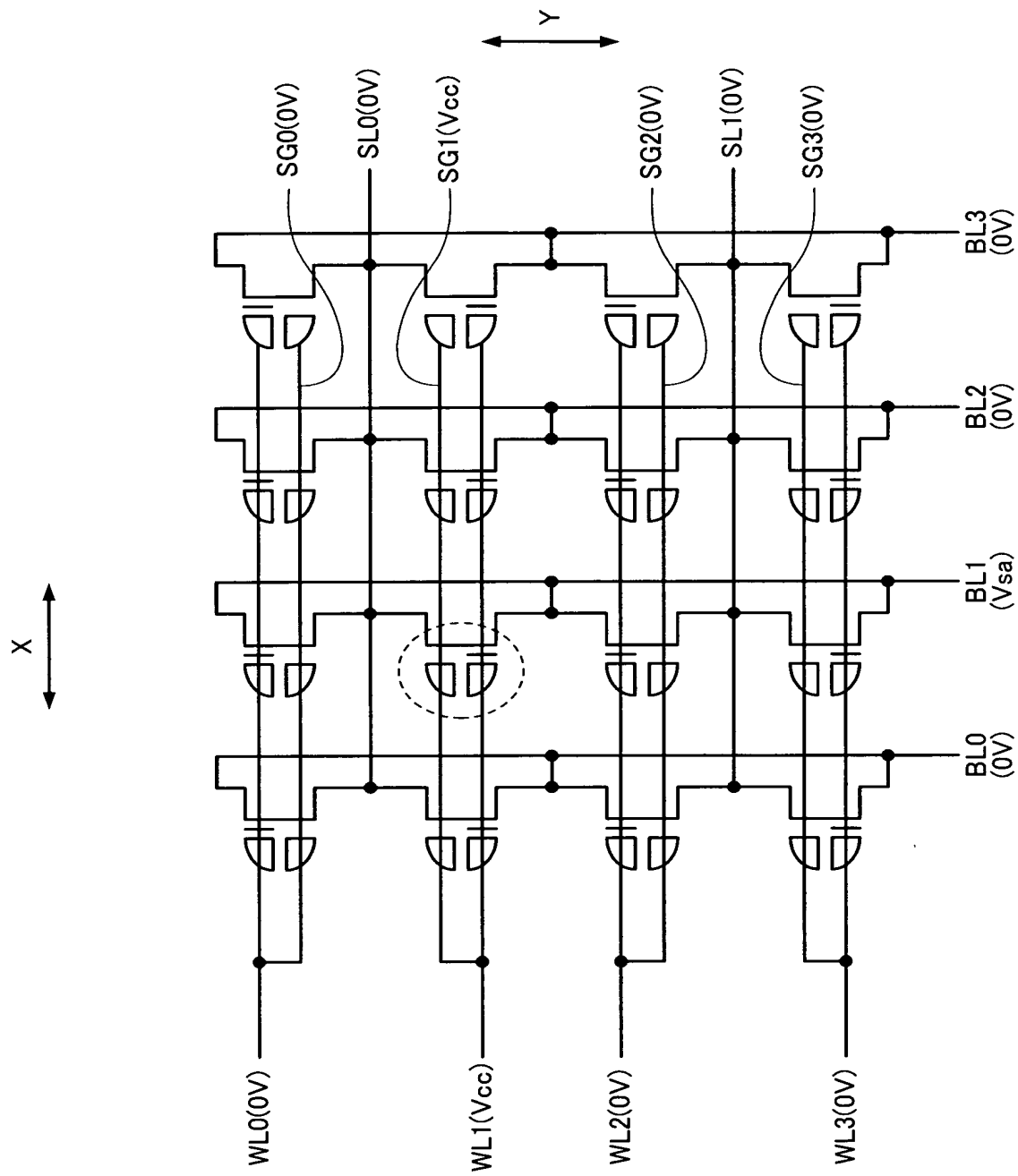


FIG. 13

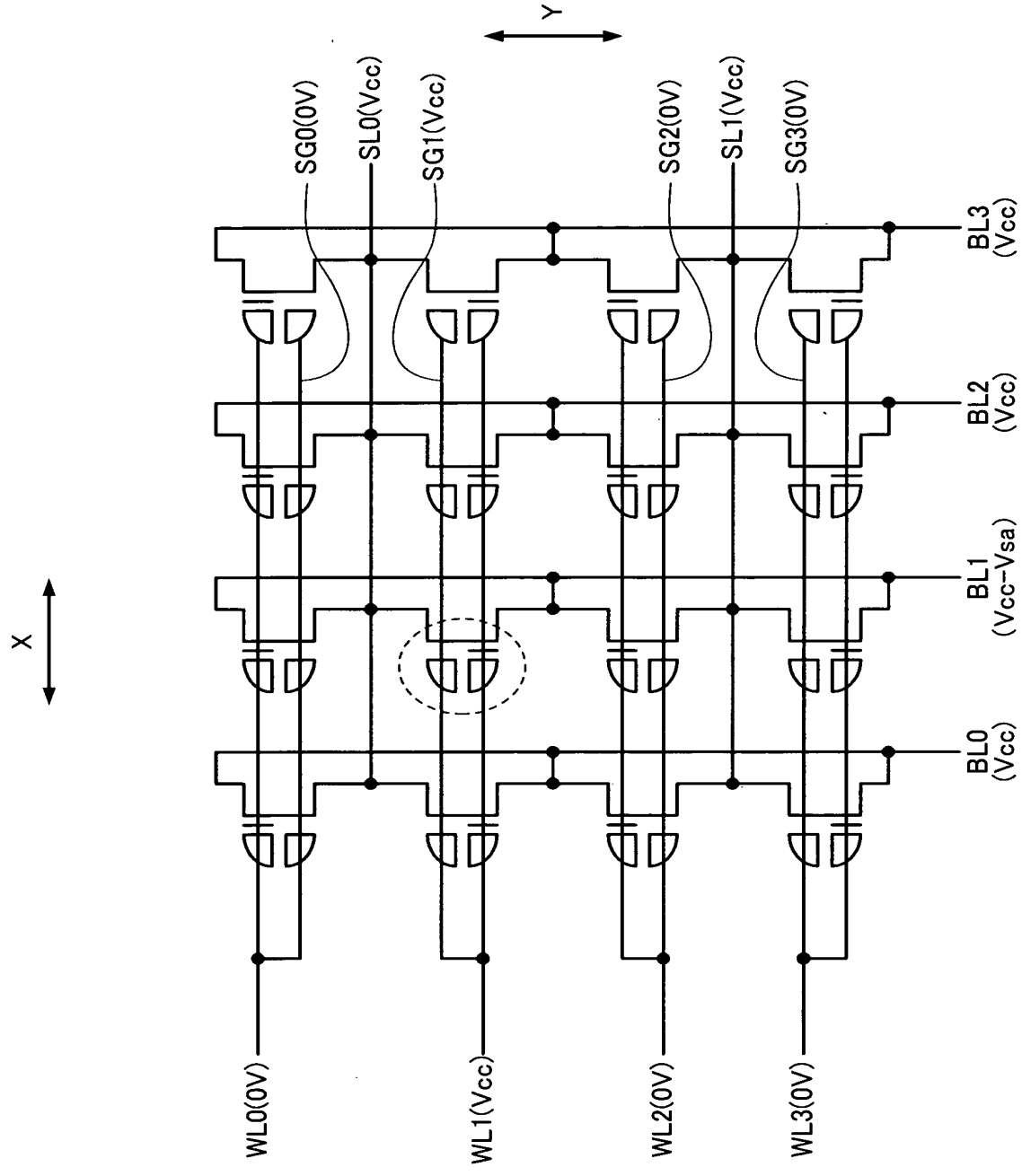


FIG. 14

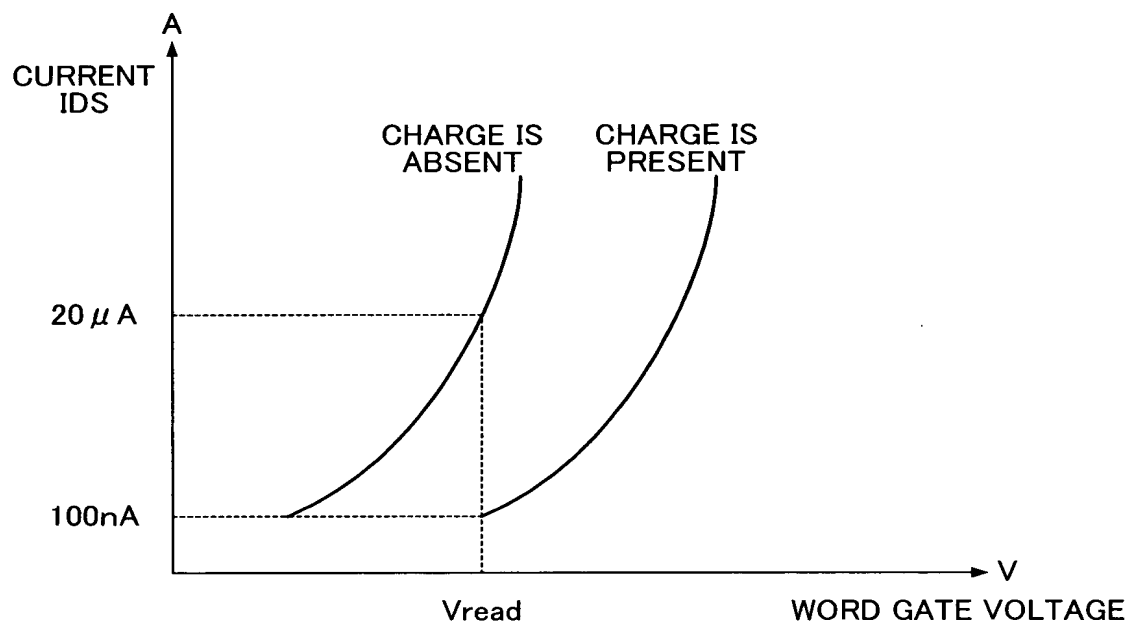


FIG. 15

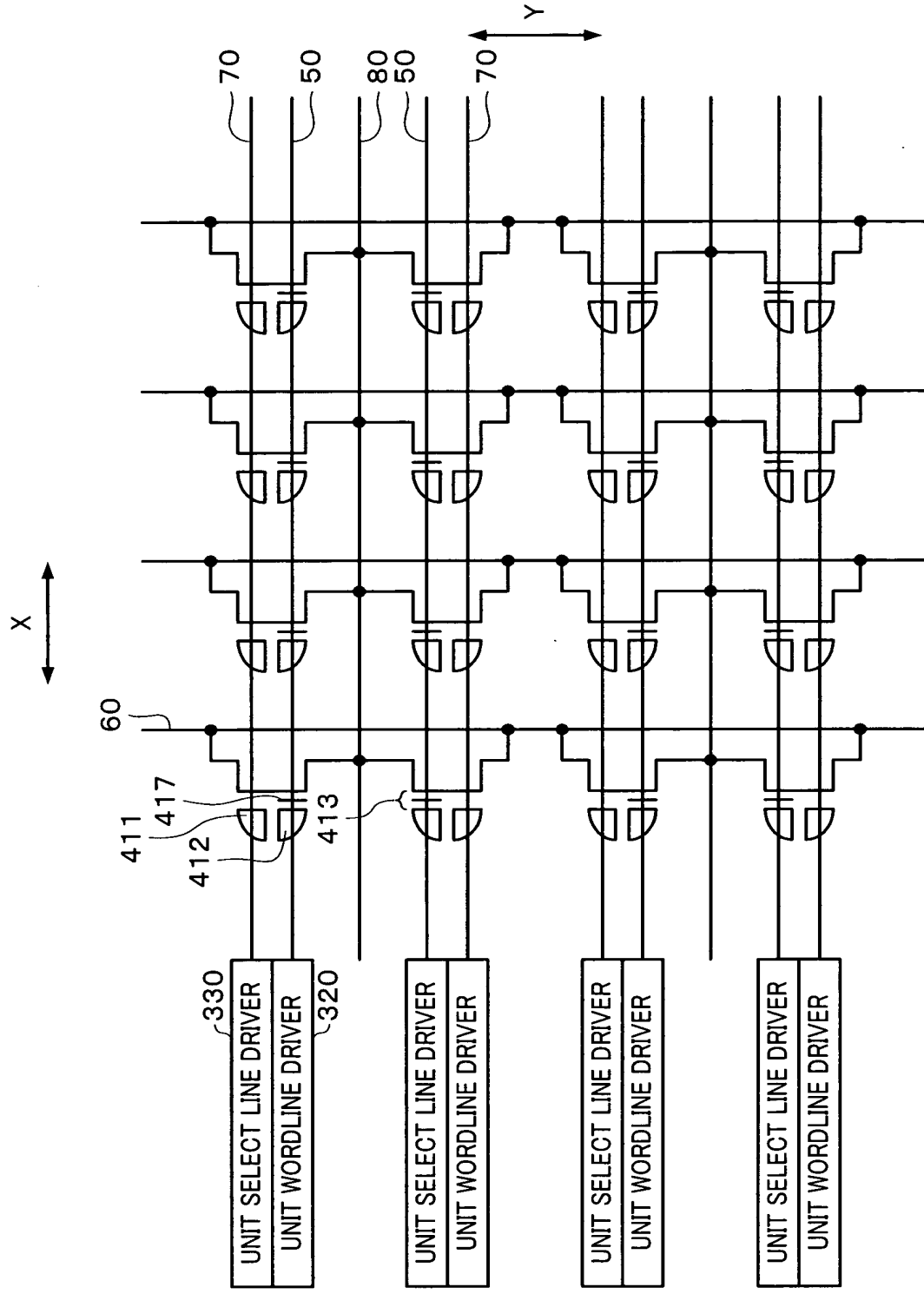


FIG. 16

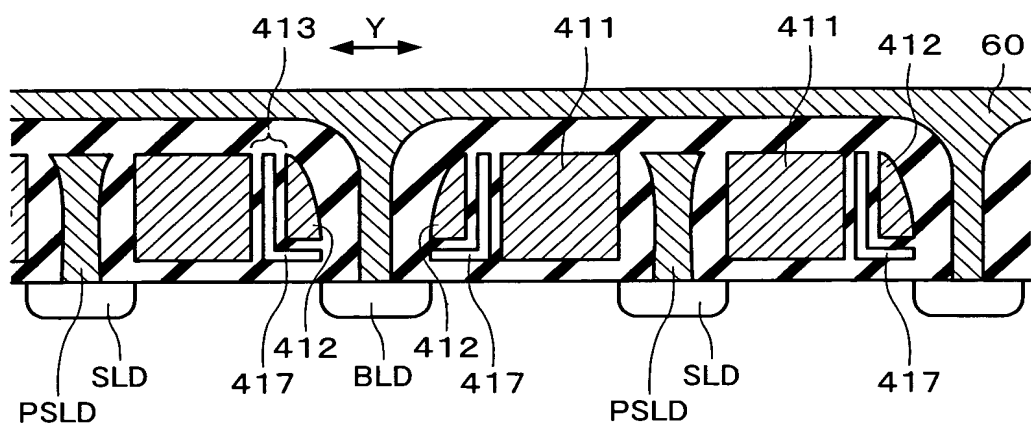




FIG. 17

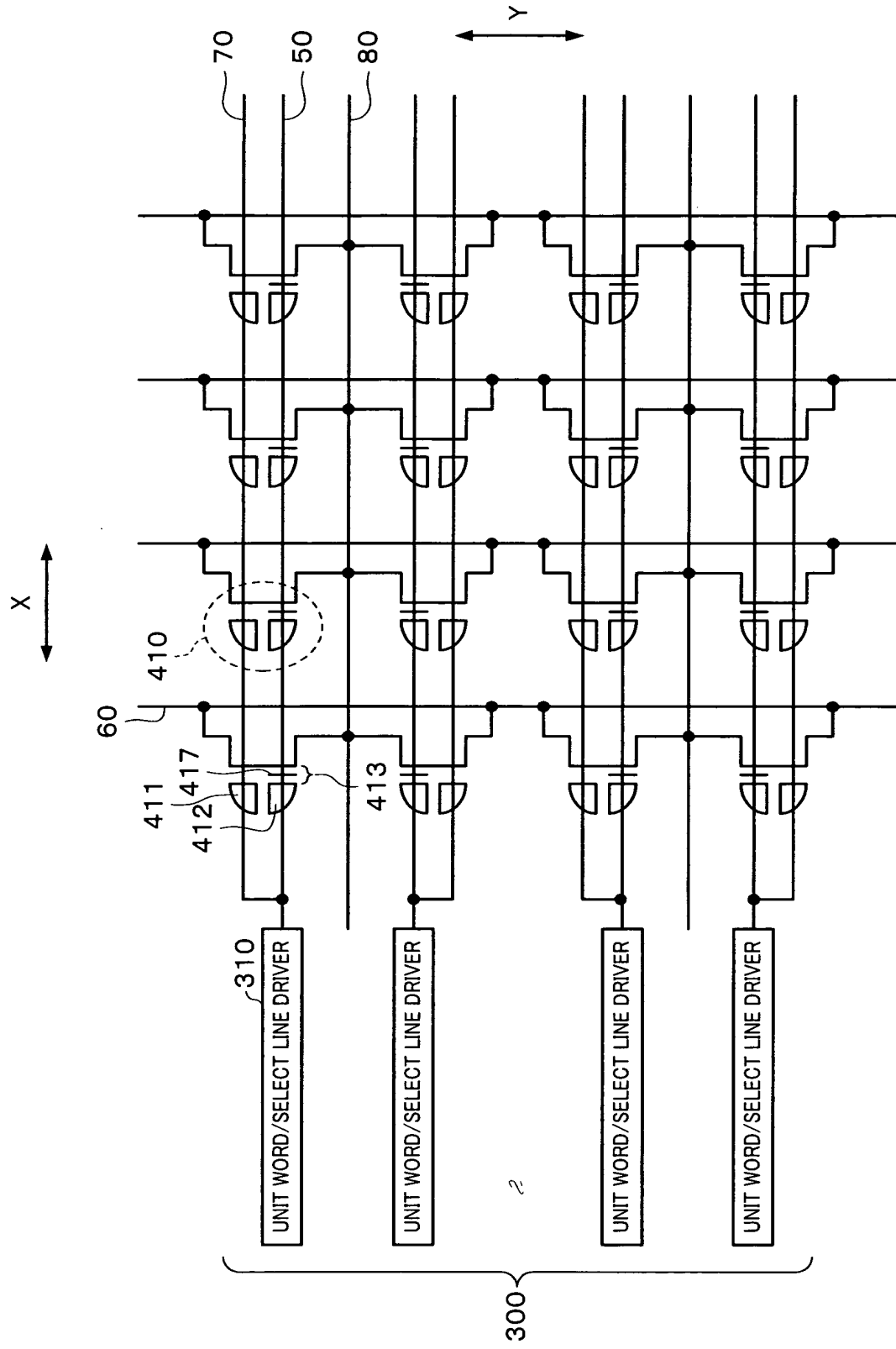


FIG. 18

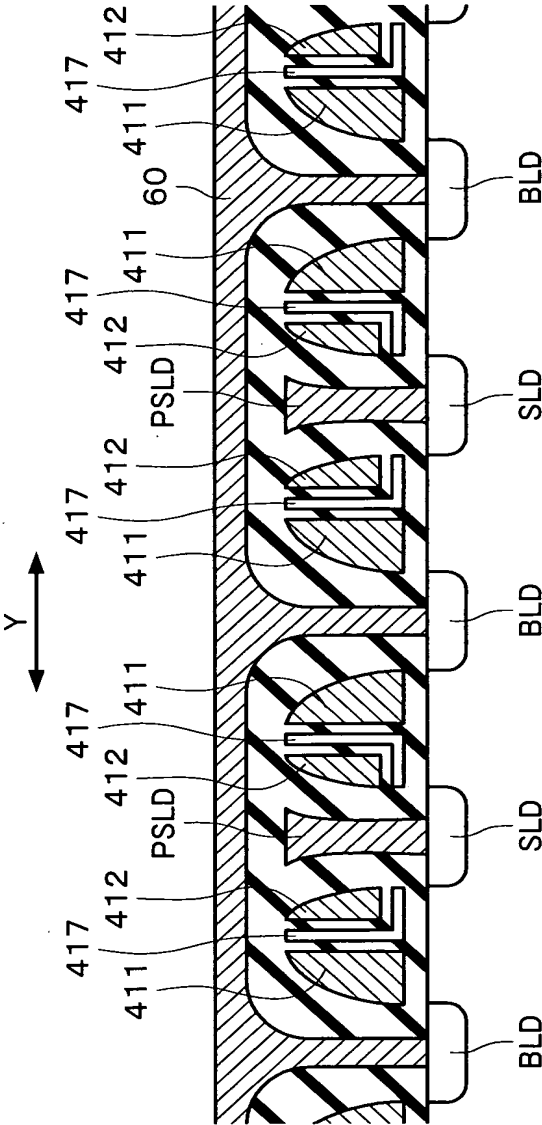




FIG. 20

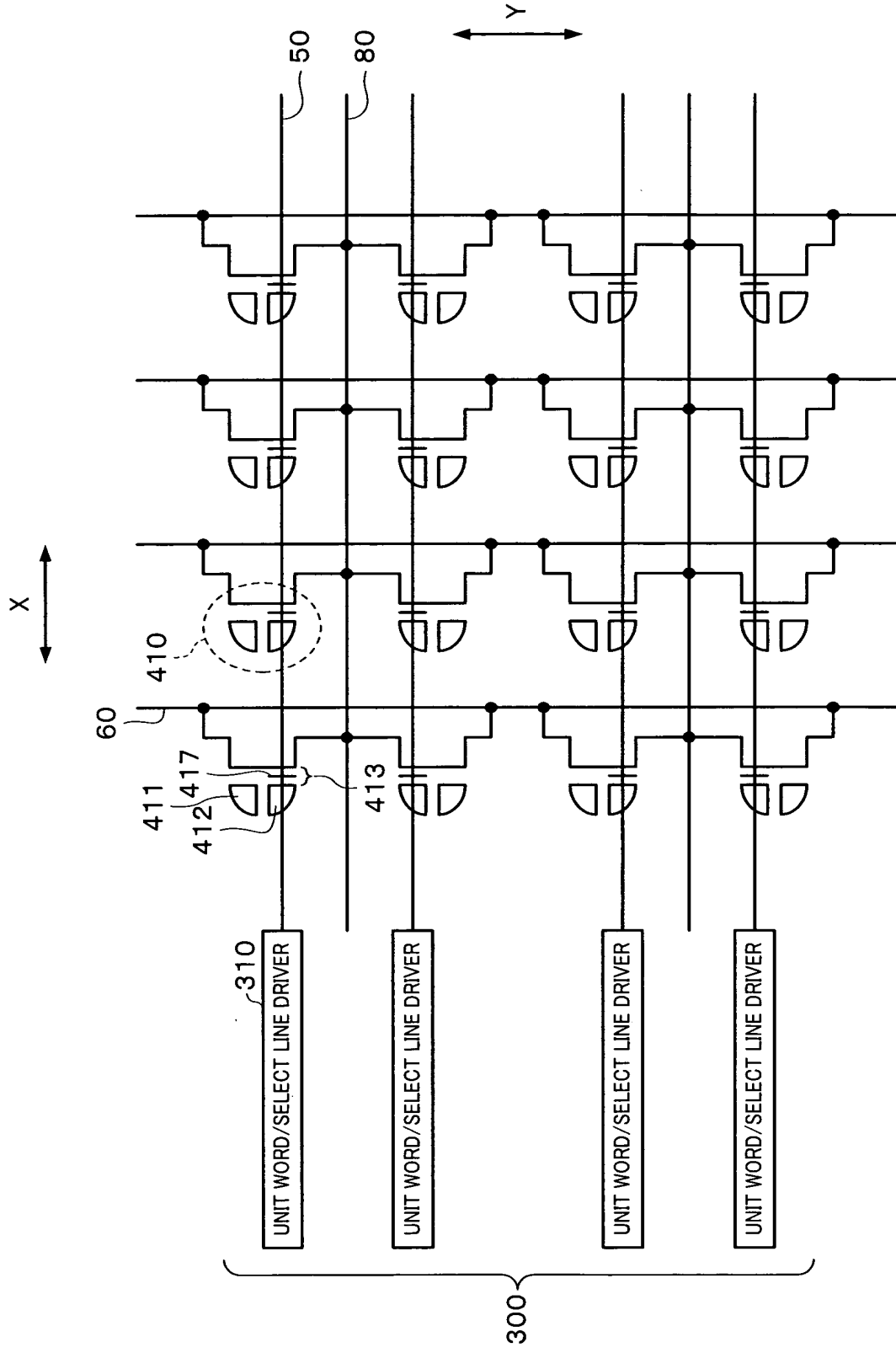


FIG. 21

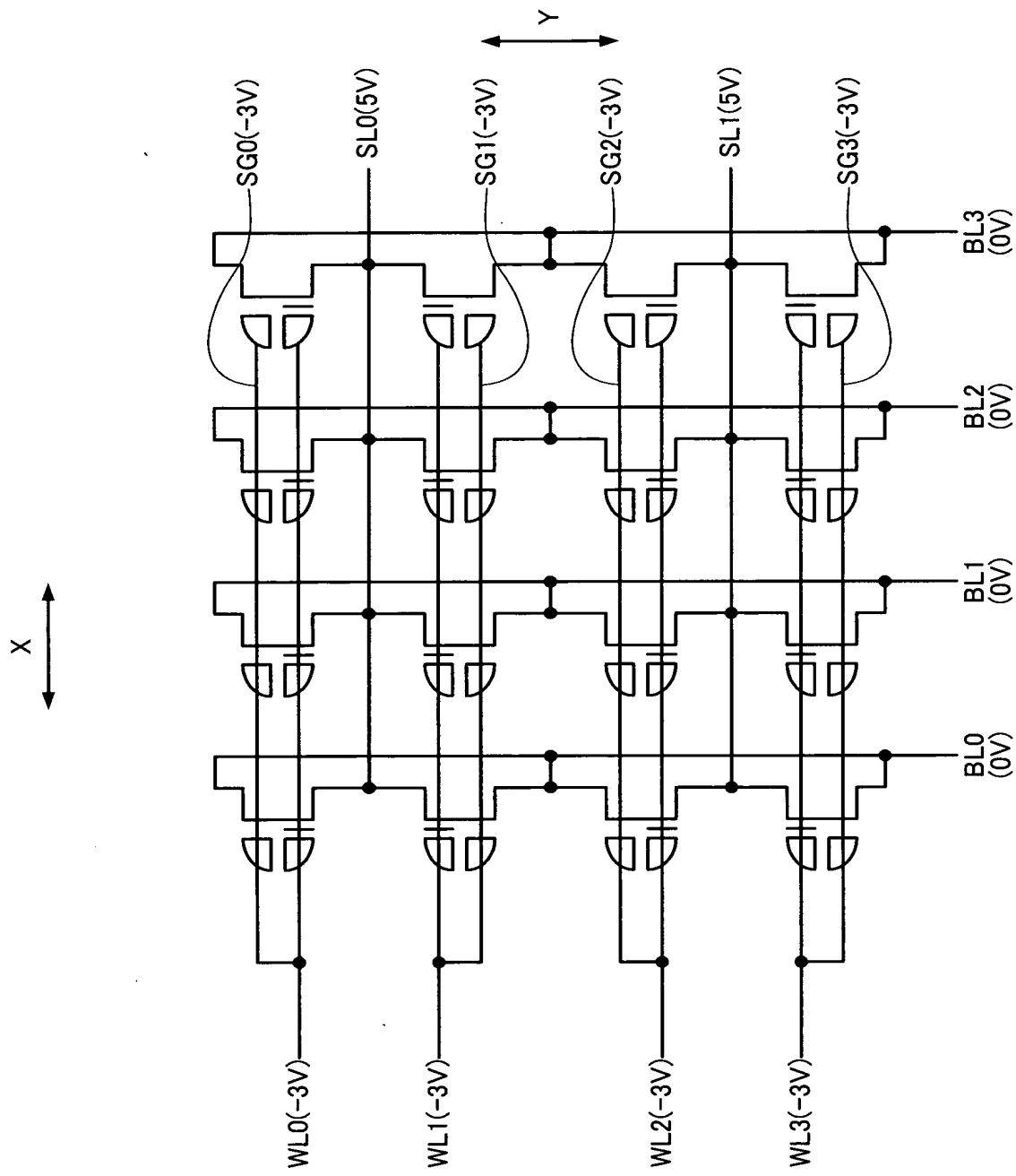


FIG. 22

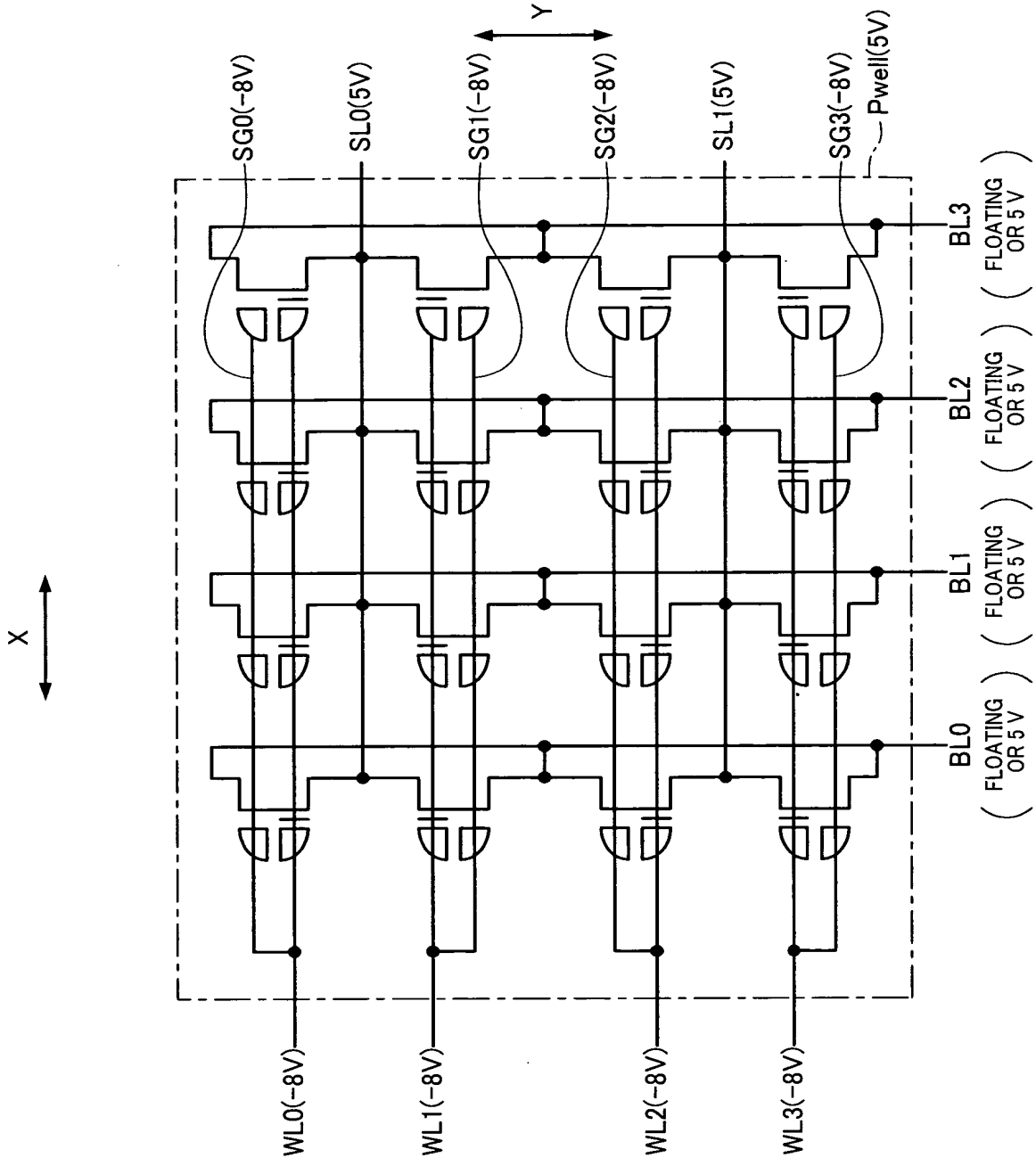


FIG. 23

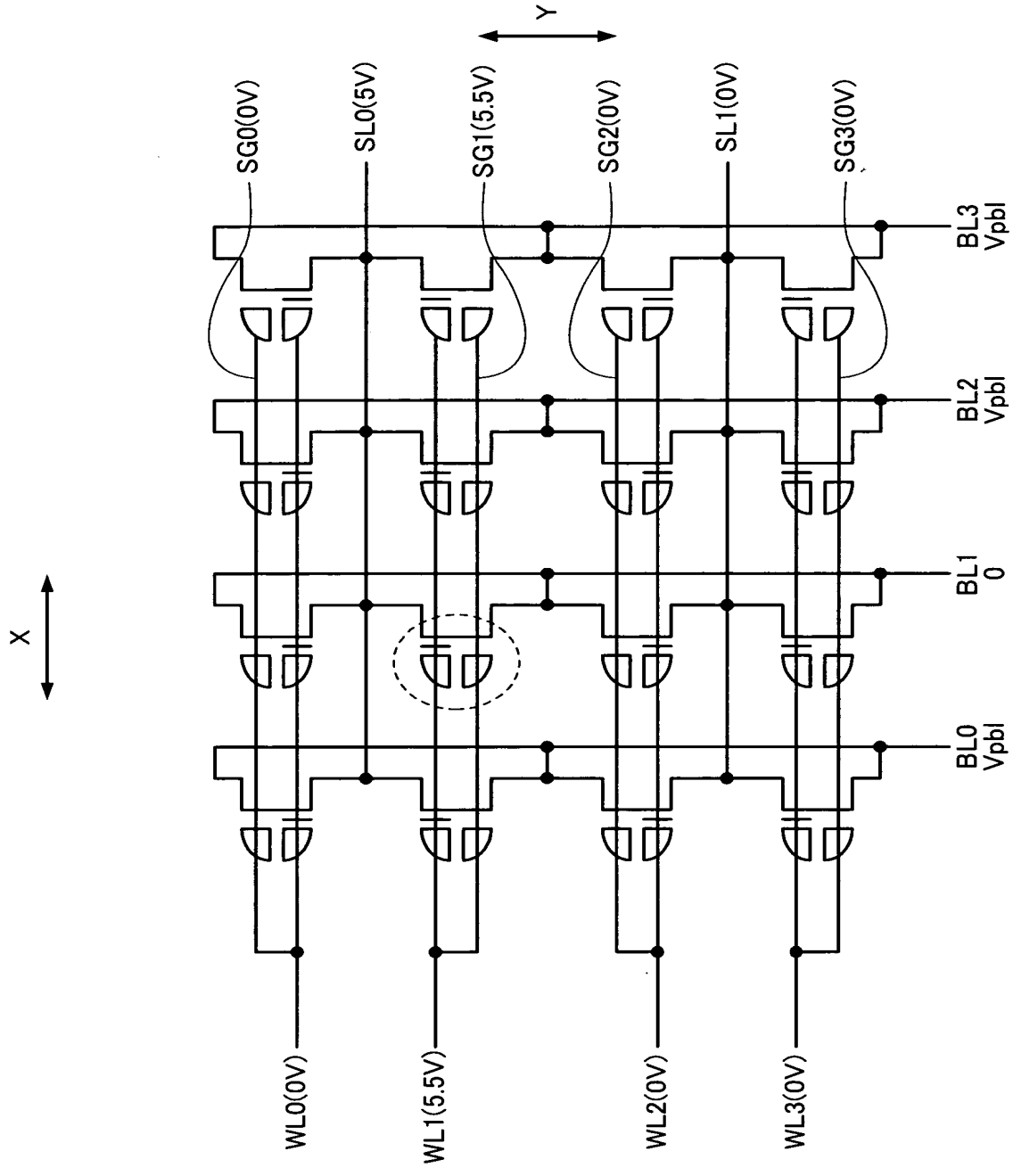


FIG. 24

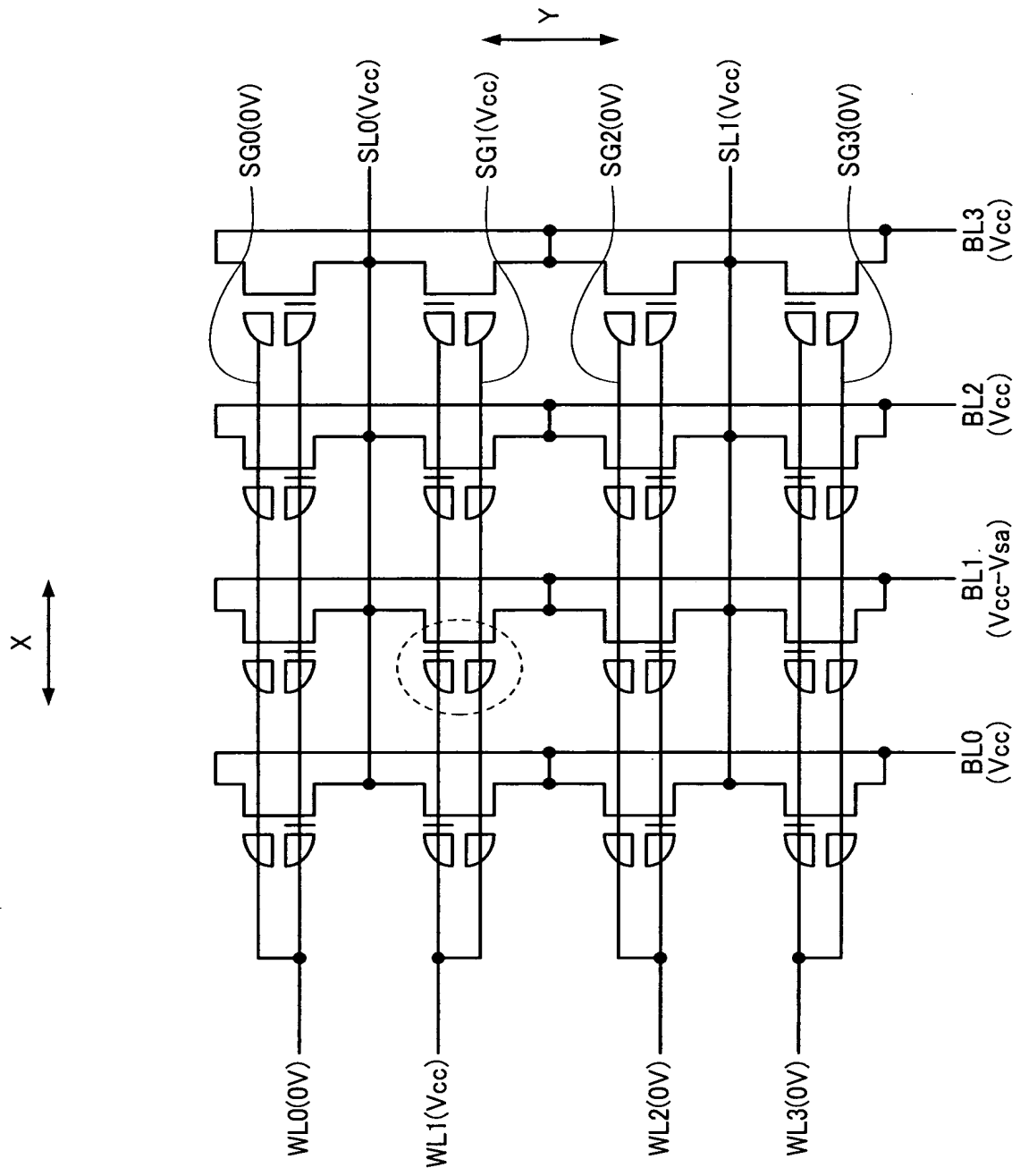




FIG. 25

